

**TITLE: POLYCRYSTALLINE SILICON CARBIDE SUPPORT FOR A
SUBSTRATE INTENDED TO RECEIVE POWER SEMICONDUCTOR DEVICES
AND SUBSTRATE COMPRISING SUCH A SUPPORT**

5

ABSTRACT

The invention relates to a polycrystalline silicon carbide support for a substrate intended to receive a power semiconductor device. The support has a first face, denoted "front face", and a second face, denoted "rear face", and comprises a first surface layer disposed directly under the front face and having resistivity that is greater than or equal to 1 ohm.cm, and a second surface layer disposed directly under the rear face and having resistivity that is strictly less than 1 ohm.cm.

Figure 3